
Abinit Project

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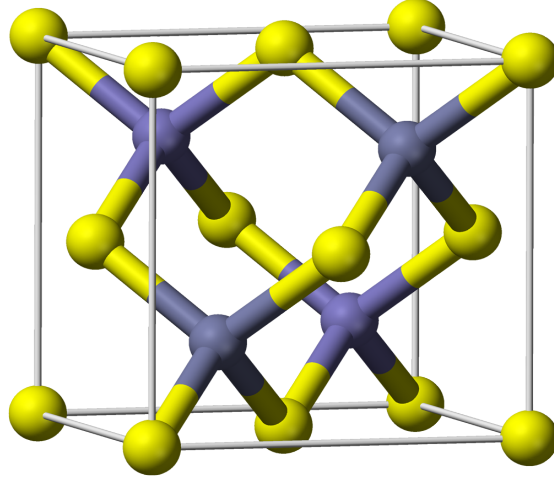
Submitted to: Dr. Kuldeep Kumar

1 Aim

To study variation in band gap of InAs by changing lattice parameter c with the using of Abinit.

2 Theory

Indium arsenide(InAs) is a narrow-bandgap semiconductor which is composed of indium and arsenic. It has FCC structure and band gap of 0.35 at room temperature.



Primitive vectors for fcc Structure

$$\vec{a}_1 = \frac{a}{2}(\hat{x} + \hat{y}); \vec{a}_2 = \frac{a}{2}(\hat{y} + \hat{z}); \vec{a}_3 = \frac{a}{2}(\hat{x} + \hat{z})$$

The Reciprocal vectors for fcc Structure

$$\vec{b}_1 = \frac{2\pi}{a}(-\hat{x} + \hat{y} + \hat{z}); \vec{b}_2 = \frac{2\pi}{a}(\hat{x} - \hat{y} + \hat{z}); \vec{b}_3 = \frac{2\pi}{a}(\hat{x} + \hat{y} - \hat{z})$$

Brillouin zone

Critical points	FCC Structure
K	Middle of an edge joining two hexagonal faces
L	Center of a hexagonal face
U	Middle of an edge joining a hexagonal and a square face
W	Corner point
X	Center of a square face

Path: L- Γ -X-W-K

kptbounds for FCC

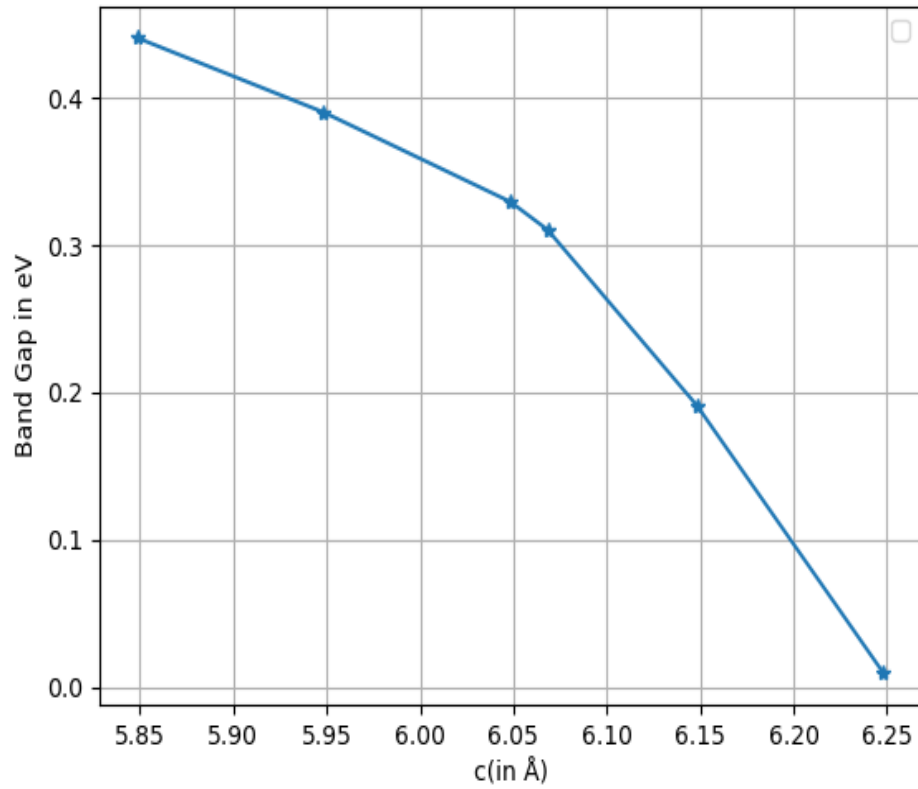
Critical Points	kptbounds
L	1/2 0 0
Γ	0 0 0
X	0 1/2 1/2
W	1/4 1/2 3/4
K	3/8 3/8 3/4

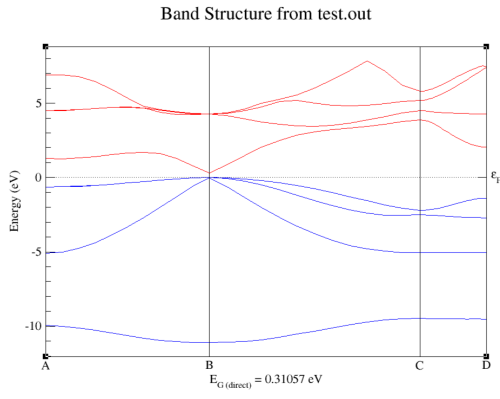
Variation of Band Gap with lattice parameter(c)

c(in Å)	Bandgap(in eV)
5.8483	0.44096
5.9483	0.39037
6.0483	0.32961
6.0583	0.329609
6.0683	0.31057
6.1483	0.19122
6.2483	0.00938

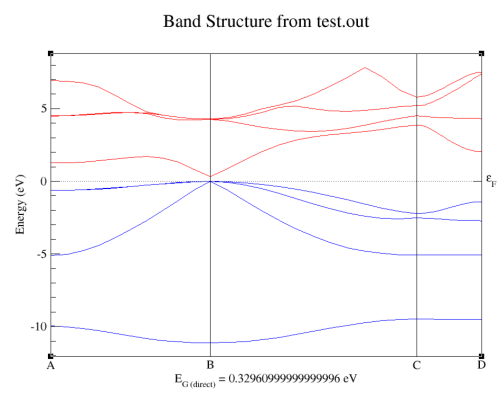
Table 1: Variation of Band Gap with c

Here, From the above table we can see that as the value of c is increased, Band Gap reduces because the interatomic distance is increased accordingly. Therefore, Force between parent atom and valence band decreases.

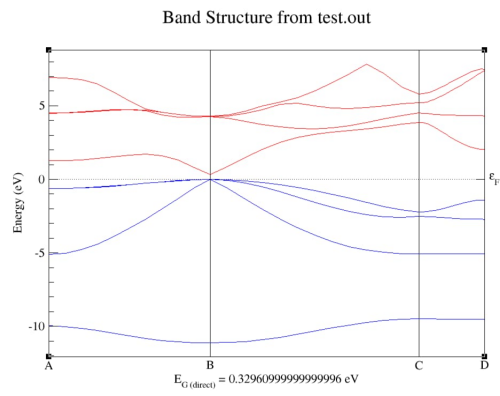




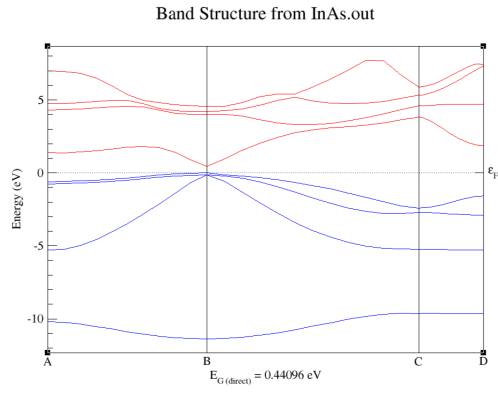
(a) $c=6.0683$



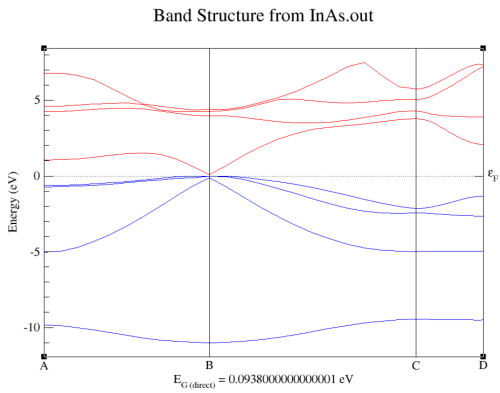
(b) $c=6.0583$



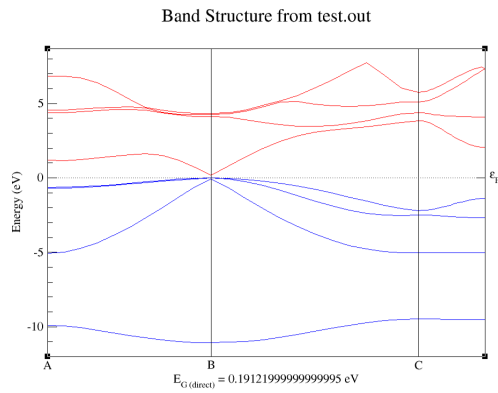
(a) $c=6.0483$



(b) $c=5.8483$



(a) $c=6.2483$



(b) $c=6.1483$